10-PC073AA030SM-PF04H06Y
datasheet

***flow*3xANPFC 0** **650 V / 30 A**

Topology features

- 3ph Advanced Neutral PFC

Component features

- High efficiency in hard switching and resonant topologies
- High speed switching
- Low gate charge

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

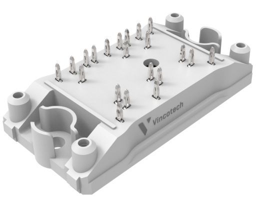
Target applications

- Embedded Drives
- Heat Pumps
- HVAC
- Industrial Drives

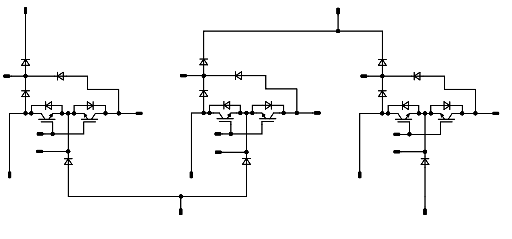
Types

- 10-PC073AA030SM-PF04H06Y

flow 0 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Negative Neutral Point Switch					
Collector-emitter voltage	V_{CES}			650	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	27	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		90	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	48	W
Gate-emitter voltage	V_{GES}			±20	V
Maximum junction temperature	T_{jmax}			175	°C
Positive Neutral Point Switch					
Collector-emitter voltage	V_{CES}			650	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	27	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		90	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	48	W
Gate-emitter voltage	V_{GES}			±20	V
Maximum junction temperature	T_{jmax}			175	°C
Negative Boost Diode					
Peak repetitive reverse voltage	V_{RRM}			600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	38	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		60	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 25 °C	330	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	45	W
Maximum junction temperature	T_{jmax}			175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Positive Boost Diode					
Peak repetitive reverse voltage	V_{RRM}			600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	38	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		60	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 25 °C	330	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	45	W
Maximum junction temperature	T_{jmax}			175	°C
Negative Neutral Point Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	31	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	200	A
Surge current capability	I^2t			200	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	37	W
Maximum junction temperature	T_{jmax}			150	°C
Positive Neutral Point Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	31	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	200	A
Surge current capability	I^2t			200	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	37	W
Maximum junction temperature	T_{jmax}			150	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Positive Boost Diode Protection Diode					
Peak repetitive reverse voltage	V_{RRM}			650	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	17	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		20	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	33	W
Maximum junction temperature	T_{jmax}			175	°C
Positive Boost Blocking Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	31	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	200	A
Surge current capability	I^2t			200	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	37	W
Maximum junction temperature	T_{jmax}			150	°C

Module Properties

Parameter	Symbol	Conditions		Value	Unit
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage	t_p = 1 min	2500	V
Creepage distance				>12,7	mm
Clearance				>12,7	mm
Comparative Tracking Index	CTI			≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Values Min	Values Typ	Values Max	Unit
Negative Neutral Point Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0003	25	3,3	4	4,7	V
Collector-emitter saturation voltage	V_{CEsat}		15		30	25 125 150		1,67 1,8 1,84	2,22(1)	V
Collector-emitter cut-off current	I_{CES}		0	650		25			40	µA
Gate-emitter leakage current	I_{GES}		20	0		25			120	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		1800		pF
Output capacitance	C_{oes}							45		pF
Reverse transfer capacitance	C_{res}							7		pF
Gate charge	Q_g	V_{CC} = 520 V	15		30	25		70		nC
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	0/15	400	30	25 125 150		33,78 31,81 31,19		ns
Rise time	t_r					25 125 150		27,26 28,63 28,69		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		204,32 224,39 228,78		ns
Fall time	t_f					25 125 150		8,89 8,68 8,6		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,542 µC Q_{rFWD}=1,52 µC Q_{rFWD}=1,87 µC				25 125 150		0,686 1,07 1,18		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,255 0,317 0,347		mWs

10-PC073AA030SM-PF04H06Y
datasheet

Vincotech

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Positive Neutral Point Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0003	25	3,3	4	4,7	V
Collector-emitter saturation voltage	V_{CEsat}		15		30	25 125 150		1,67 1,8 1,84	2,22[1]	V
Collector-emitter cut-off current	I_{CES}		0	650		25			40	µA
Gate-emitter leakage current	I_{GES}		20	0		25			120	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		1800		pF
Output capacitance	C_{oes}							45		pF
Reverse transfer capacitance	C_{res}							7		pF
Gate charge	Q_g	V_{CC} = 520 V	15		30	25		70		nC
Thermal										
Thermal resistance junction to sink [2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 16 Ω R_{goff} = 64 Ω	0/15	400	30	25 125 150		34 31,12 30,91		ns
Rise time	t_r					25 125 150		34,57 35,51 35,19		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		646,93 699,36 712,09		ns
Fall time	t_f					25 125 150		85,64 92,53 95,4		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,516 µC Q_{rFWD}=1,39 µC Q_{rFWD}=1,7 µC				25 125 150		0,701 1,06 1,18		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		1,18 1,2 1,24		mWs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Negative Boost Diode										
Static										
Forward voltage	V_F				30	25 125 150		1,39 1,2 1,14	2(1)	V
Reverse leakage current	I_R	V_r = 600 V				25			20	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,12		K/W
Dynamic										
Peak recovery current	I_{RM}	d*i*/d*t*=1616 A/µs d*i*/d*t*=1406 A/µs d*i*/d*t*=1370 A/µs	0/15	400	30	25 125 150		22,37 34,7 39,77		A
Reverse recovery time	t_{rr}					25 125 150		45,85 70,4 77,69		ns
Recovered charge	Q_r					25 125 150		0,542 1,52 1,87		µC
Reverse recovered energy	E_{rec}					25 125 150		0,069 0,234 0,298		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		620,75 1316,54 1333,69		A/µs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Positive Boost Diode										
Static										
Forward voltage	V_F				30	25 125 150		1,39 1,2 1,14	2(1)	V
Reverse leakage current	I_R	V_r = 600 V				25			20	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,12		K/W
Dynamic										
Peak recovery current	I_{RM}	d*i*/d*t*=1226 A/µs d*i*/d*t*=1138 A/µs d*i*/d*t*=1163 A/µs	0/15	400	30	25 125 150		20,13 32,83 37,54		A
Reverse recovery time	t_{rr}					25 125 150		44,55 67,28 74,54		ns
Recovered charge	Q_r					25 125 150		0,516 1,39 1,7		µC
Reverse recovered energy	E_{rec}					25 125 150		0,068 0,21 0,264		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		702,76 1591,16 1552,43		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Negative Neutral Point Diode										
Static										
Forward voltage	V_F				18	25 125 150		1,11 1,03 1,02	1,5(1)	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 1000	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,87		K/W
Positive Neutral Point Diode										
Static										
Forward voltage	V_F				18	25 125 150		1,11 1,03 1,02	1,5(1)	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 1000	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,87		K/W

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Positive Boost Diode Protection Diode										
Static										
Forward voltage	V_F				10	25 125	1,23	1,67 1,56	1,87(1)	V
Reverse leakage current	I_R	V_r = 650 V				25			0,14	μA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,87		K/W
Positive Boost Blocking Diode										
Static										
Forward voltage	V_F				18	25 125 150		1,11 1,03 1,02	1,5(1)	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 1000	μA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,87		K/W

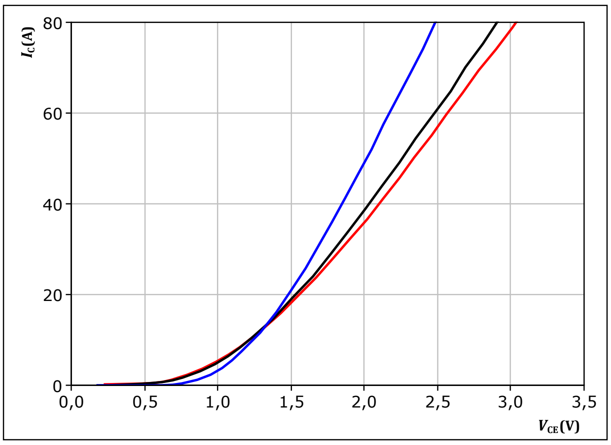
(1) Value at chip level
(2) Only valid with pre-applied Vincotech thermal interface material.

Negative Neutral Point Switch Characteristics

figure 1. IGBT

Typical output characteristics

I_C = f(V_{CE})

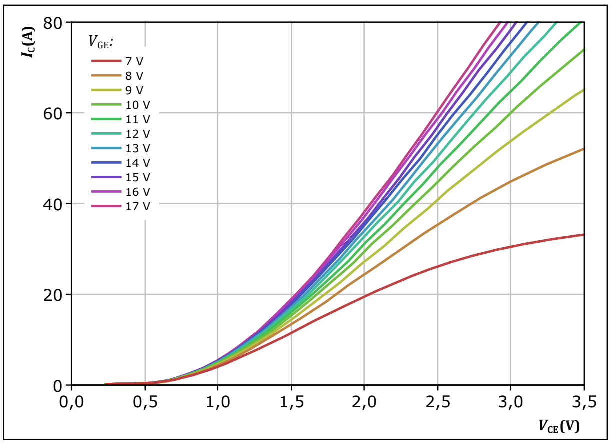


t_p =	250	µs		25 °C
V_{GE} =	15	V	T_j:	125 °C
				150 °C

figure 2. IGBT

Typical output characteristics

I_C = f(V_{CE})



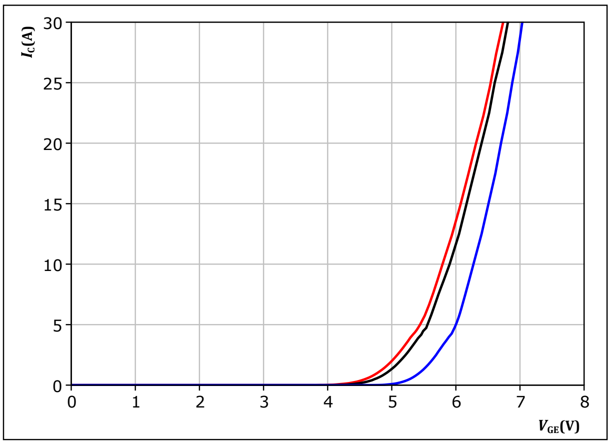
t_p =	250	µs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

I_C = f(V_{GE})

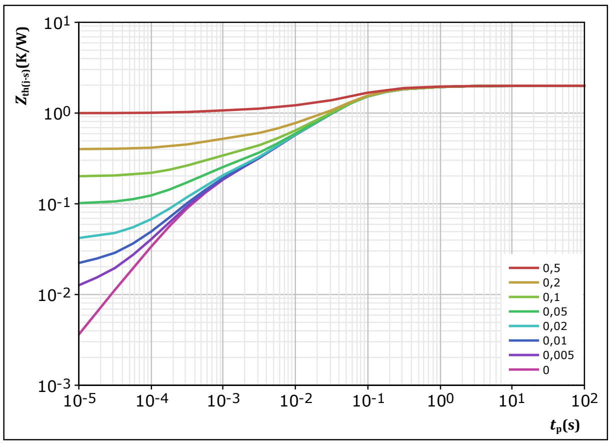


t_p =	250	µs		25 °C
V_{CE} =	10	V	T_j:	125 °C
				150 °C

figure 4. IGBT

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D =	t_p / T	
$R_{th(j-s)}$ =	1,997	K/W

IGBT thermal model values

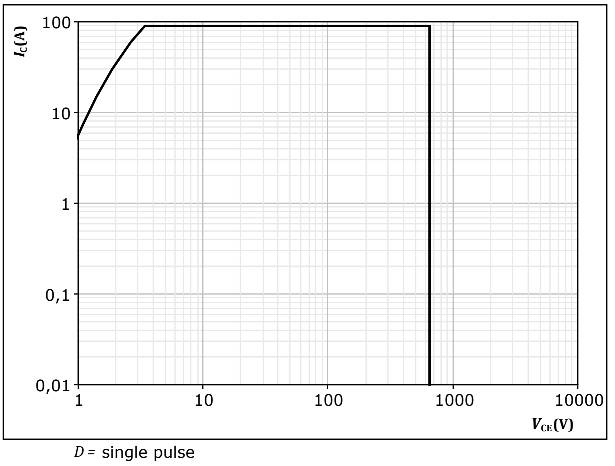
R (K/W)	τ (s)
1,14E-01	1,42E+00
3,93E-01	1,82E-01
1,10E+00	4,78E-02
2,59E-01	5,78E-03
1,35E-01	4,53E-04

Negative Neutral Point Switch Characteristics

figure 5. **IGBT**

Safe operating area

I_C = f(V_{CE})

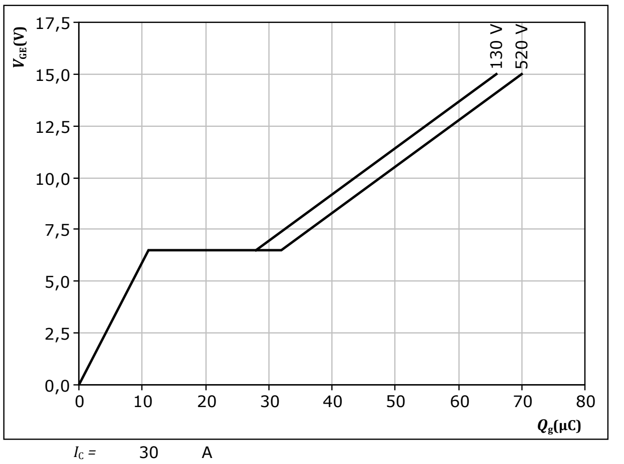


D = single pulse
T_s = 80 °C
V_{GE} = 15 V
T_j = T_{jmax}

figure 6. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



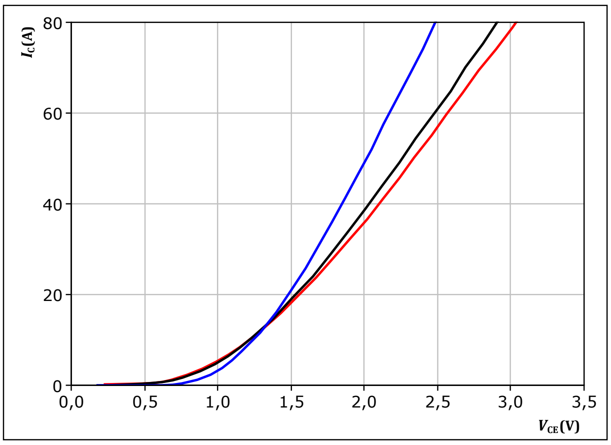
I_C = 30 A
T_j = 25 °C

Positive Neutral Point Switch Characteristics

figure 7. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

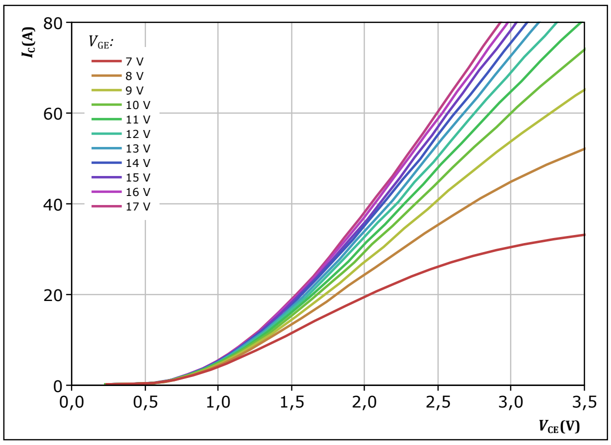


t_p =	250	µs		25 °C
V_{GE} =	15	V	T_j:	125 °C
				150 °C

figure 8. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



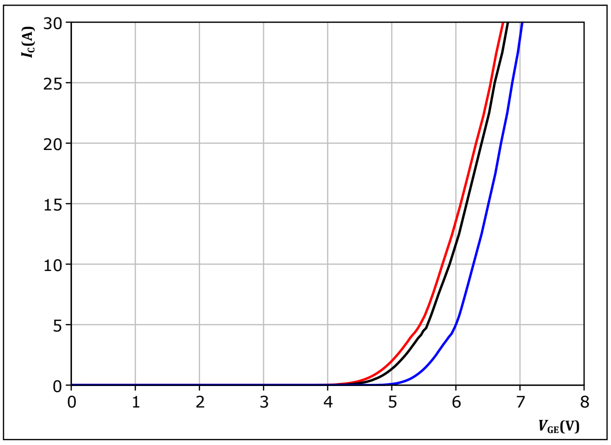
t_p =	250	µs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 9. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})

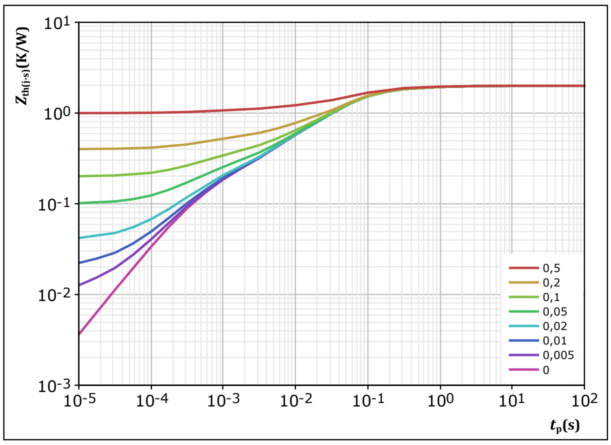


t_p =	250	µs		25 °C
V_{CE} =	10	V	T_j:	125 °C
				150 °C

figure 10. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j\text{-}s)}$ = f(t_p)



D =	t_p / T	
$R_{th(j\text{-}s)}$ =	1,997	K/W

IGBT thermal model values

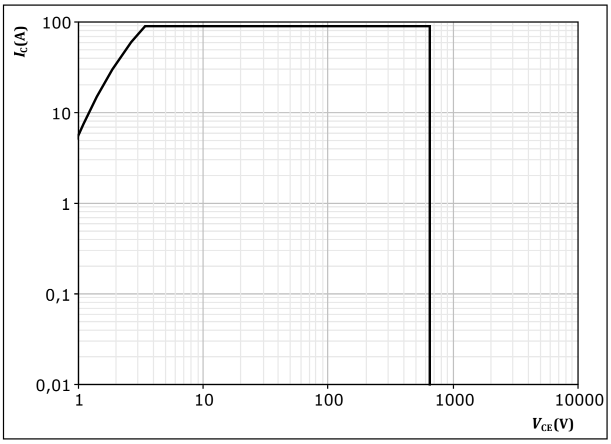
R (K/W)	τ (s)
1,14E-01	1,42E+00
3,93E-01	1,82E-01
1,10E+00	4,78E-02
2,59E-01	5,78E-03
1,35E-01	4,53E-04

Positive Neutral Point Switch Characteristics

figure 11. **IGBT**

Safe operating area

I_C = f(V_{CE})

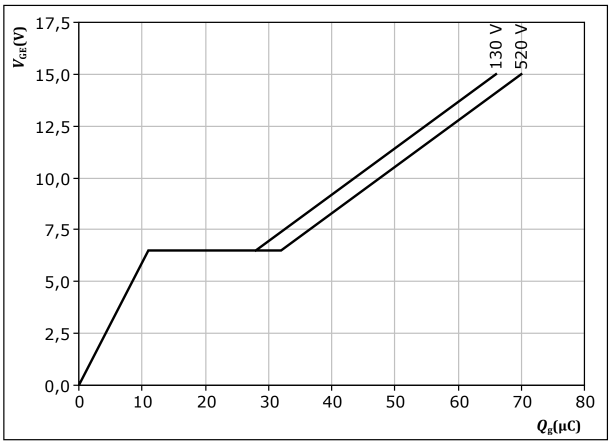


D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

figure 12. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



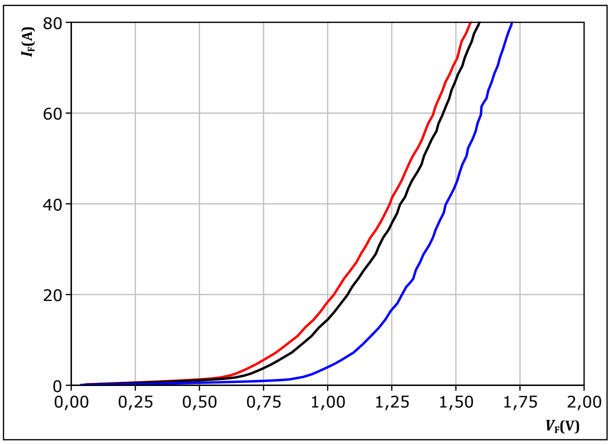
I_C =	30	A
T_j =	25	°C

Negative Boost Diode Characteristics

figure 13. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



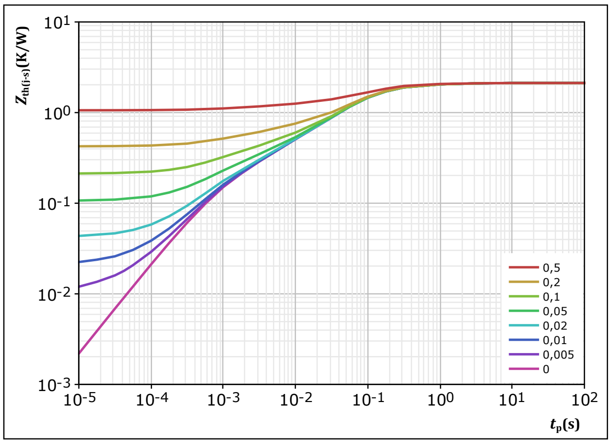
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 14. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$

$R_{th(j-s)}$ = 2,12 K/W

FWD thermal model values

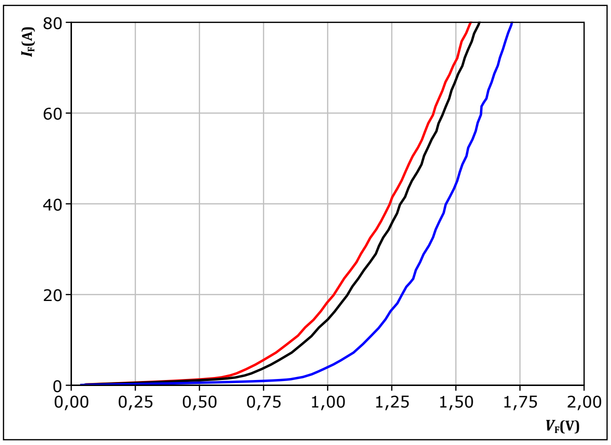
R (K/W)	τ (s)
1,00E-01	1,94E+00
3,45E-01	3,11E-01
1,29E+00	7,10E-02
2,38E-01	7,05E-03
1,48E-01	8,81E-04

Positive Boost Diode Characteristics

figure 15. **FWD**

Typical forward characteristics

I_F = f(V_F)



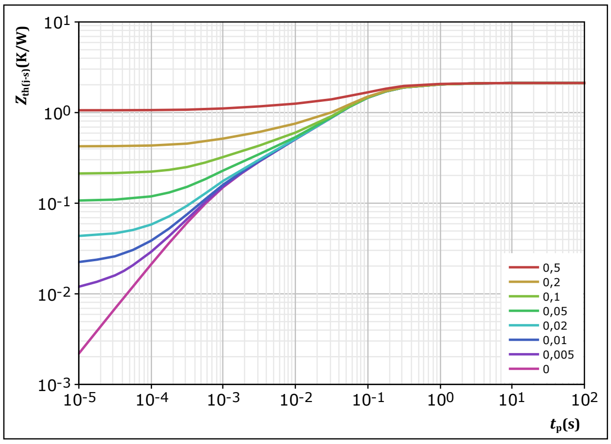
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 16. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 2,12 K/W

FWD thermal model values

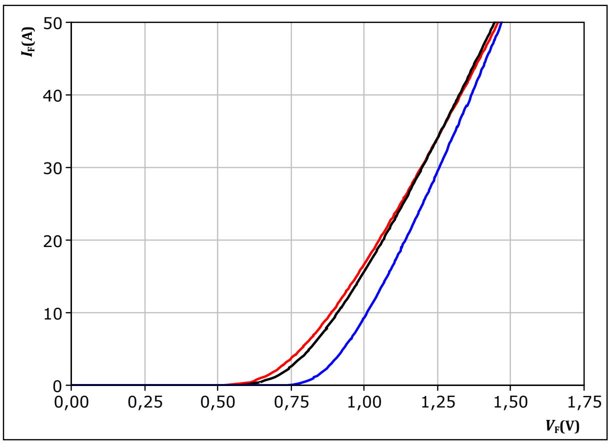
R (K/W)	τ (s)
1,00E-01	1,94E+00
3,45E-01	3,11E-01
1,29E+00	7,10E-02
2,38E-01	7,05E-03
1,48E-01	8,81E-04

Negative Neutral Point Diode Characteristics

figure 17. **Rectifier**

Typical forward characteristics

$I_F = f(V_F)$



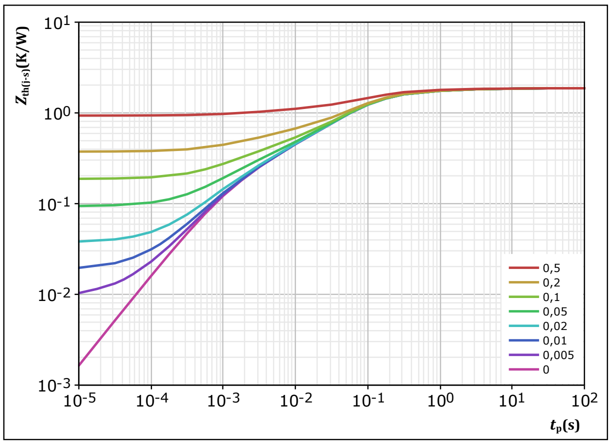
$t_p =$ 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 18. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D =$ t_p / T

$R_{th(j-s)} =$ 1,869 K/W

Rectifier thermal model values

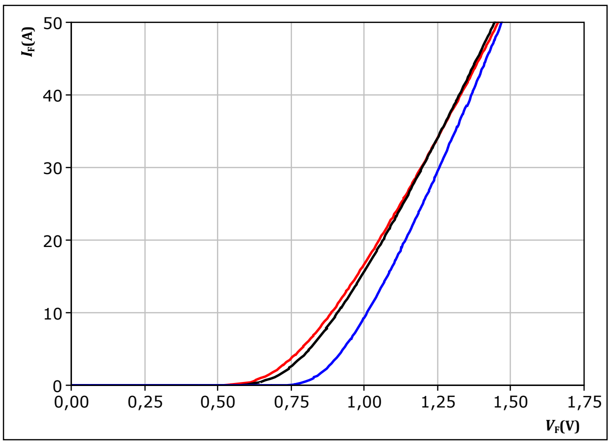
R (K/W)	τ (s)
5,65E-02	8,90E+00
1,70E-01	1,08E+00
6,15E-01	1,58E-01
6,94E-01	5,21E-02
2,16E-01	6,16E-03
1,19E-01	1,06E-03

Positive Neutral Point Diode Characteristics

figure 19. **Rectifier**

Typical forward characteristics

I_F = f(V_F)



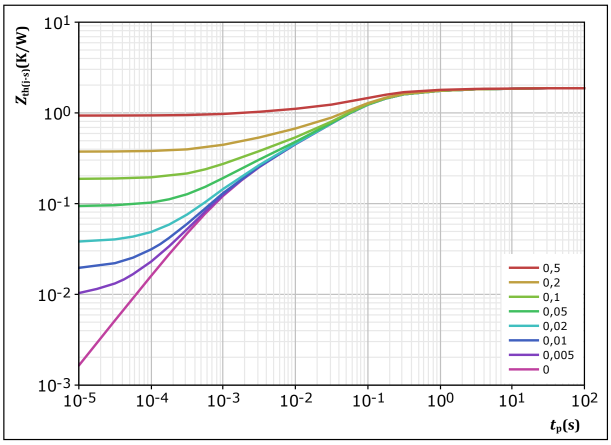
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 20. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,869 K/W

Rectifier thermal model values

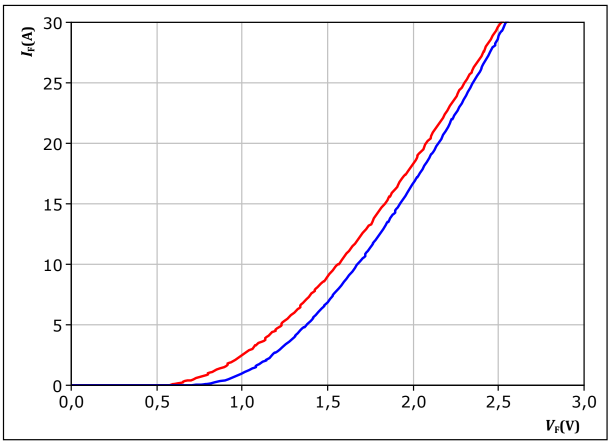
R (K/W)	τ (s)
5,65E-02	8,90E+00
1,70E-01	1,08E+00
6,15E-01	1,58E-01
6,94E-01	5,21E-02
2,16E-01	6,16E-03
1,19E-01	1,06E-03

Positive Boost Diode Protection Diode Characteristics

figure 21. FWD

Typical forward characteristics

I_F = f(V_F)



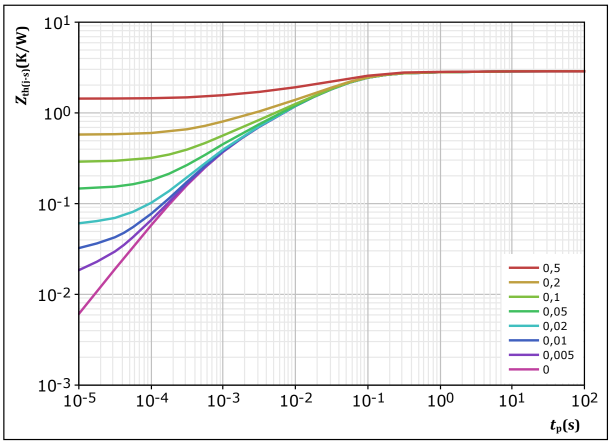
t_p = 250 µs

T_j: 25 °C, 125 °C

figure 22. FWD

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 2,873 K/W

FWD thermal model values

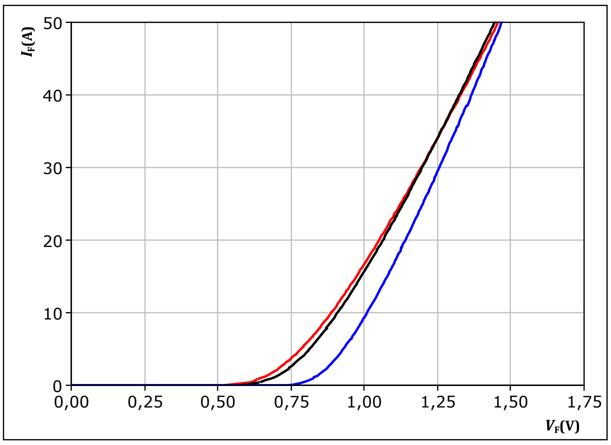
R (K/W)	τ (s)
6,53E-02	3,94E+00
1,48E-01	4,48E-01
1,31E+00	5,96E-02
7,32E-01	1,36E-02
4,04E-01	2,79E-03
2,11E-01	5,37E-04

Positive Boost Blocking Diode Characteristics

figure 23. **Rectifier**

Typical forward characteristics

$I_F = f(V_F)$



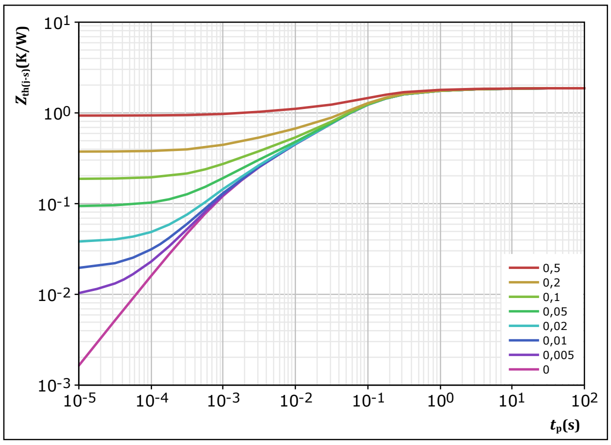
t_p = 250 μs

T_j: 25 °C, 125 °C, 150 °C

figure 24. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,869 K/W

Rectifier thermal model values

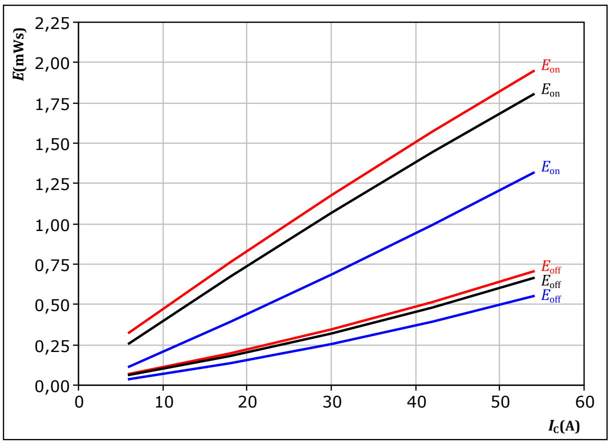
R (K/W)	τ (s)
5,65E-02	8,90E+00
1,70E-01	1,08E+00
6,15E-01	1,58E-01
6,94E-01	5,21E-02
2,16E-01	6,16E-03
1,19E-01	1,06E-03

Negative Neutral Point Switching Characteristics

figure 25. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



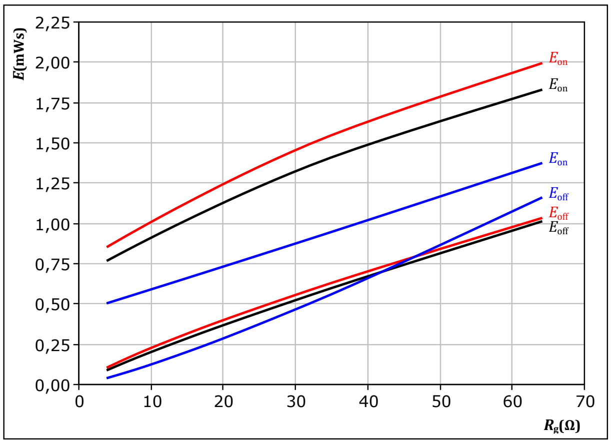
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C
R_{goff} =	16	Ω		

figure 26. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



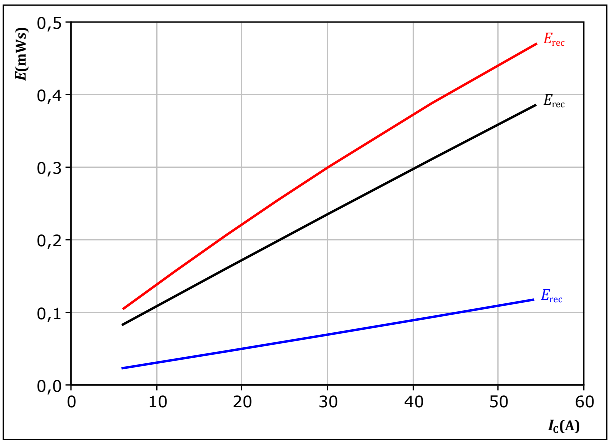
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

figure 27. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



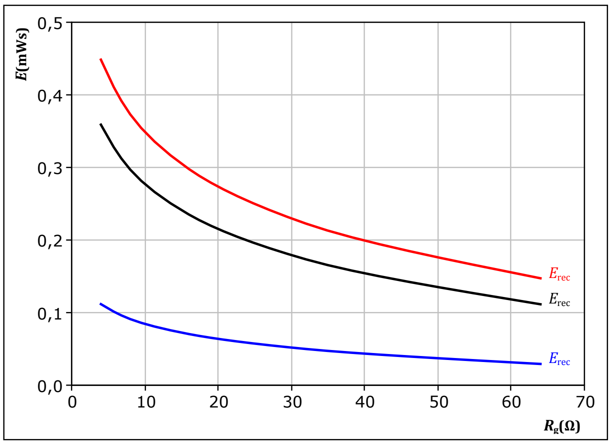
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 28. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

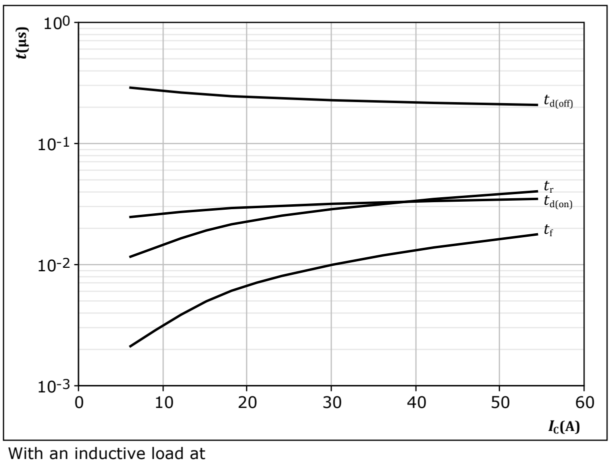
V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

Negative Neutral Point Switching Characteristics

figure 29. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



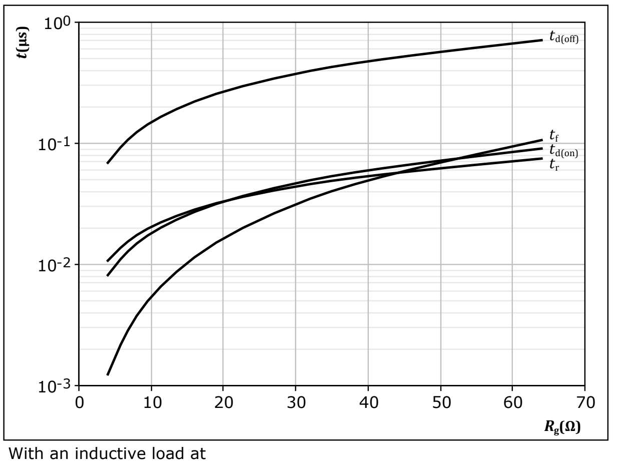
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 30. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



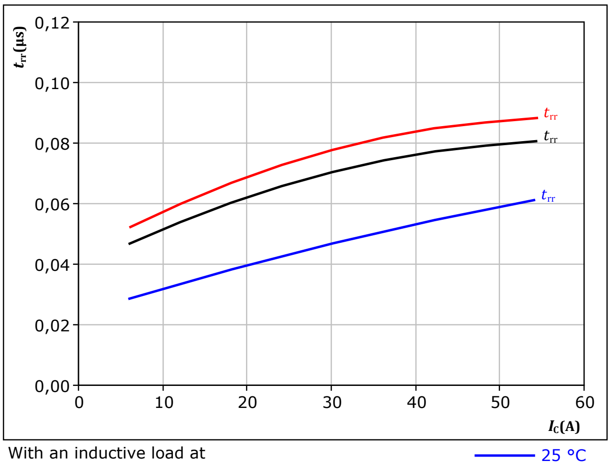
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	30	A

figure 31. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

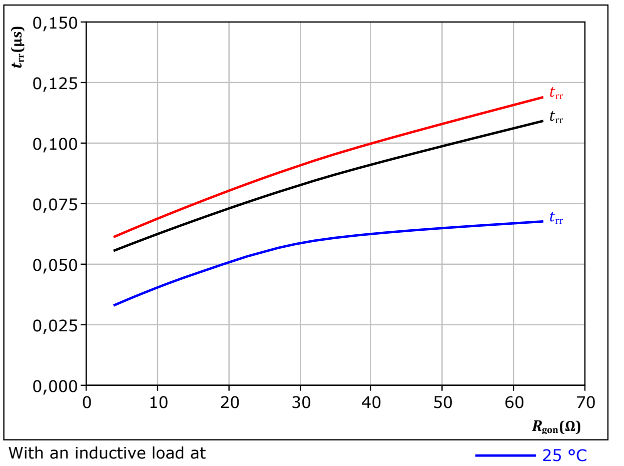
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	16	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 32. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	30	A

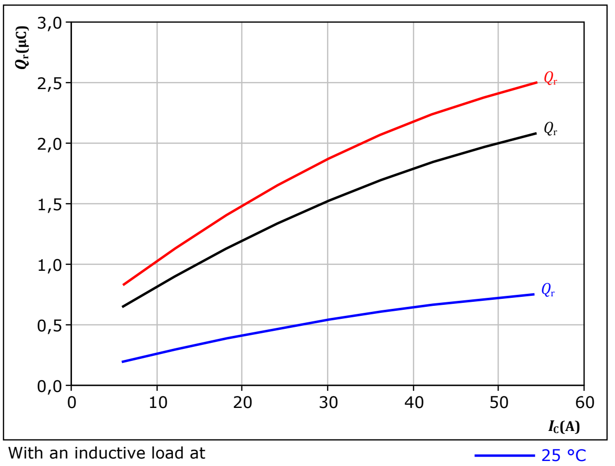
T_j: 25 °C, 125 °C, 150 °C

Negative Neutral Point Switching Characteristics

figure 33. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



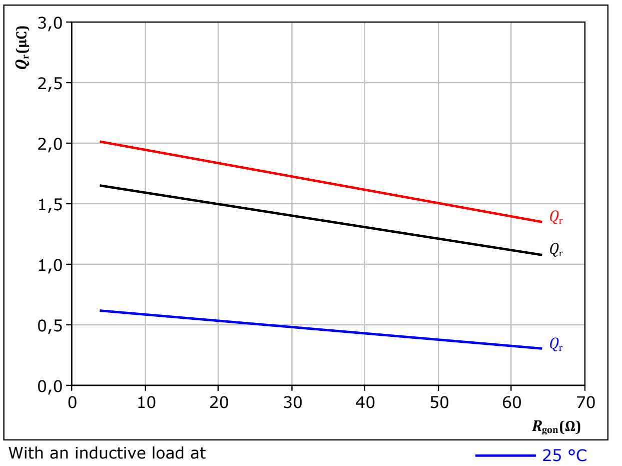
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 34. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



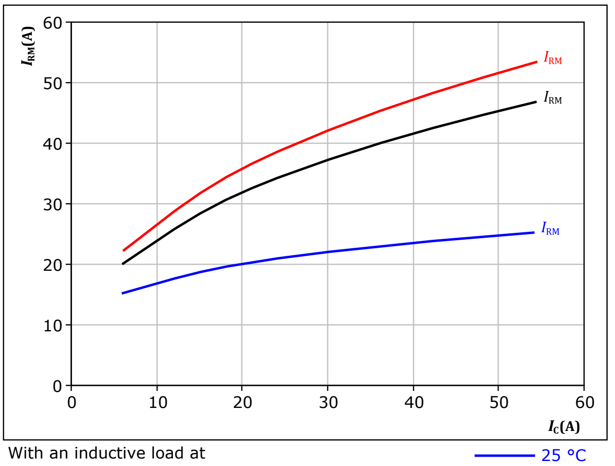
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

figure 35. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



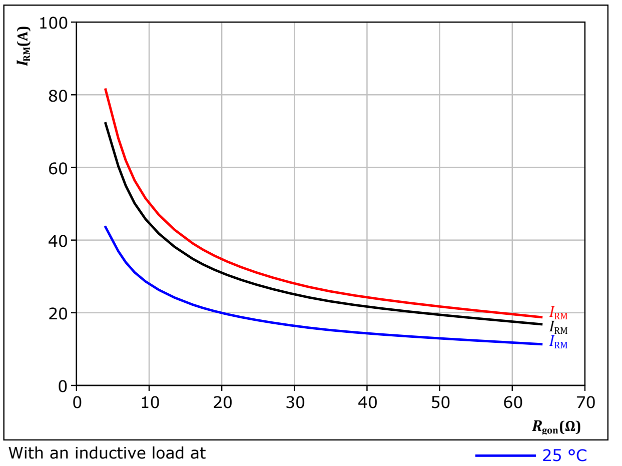
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 36. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

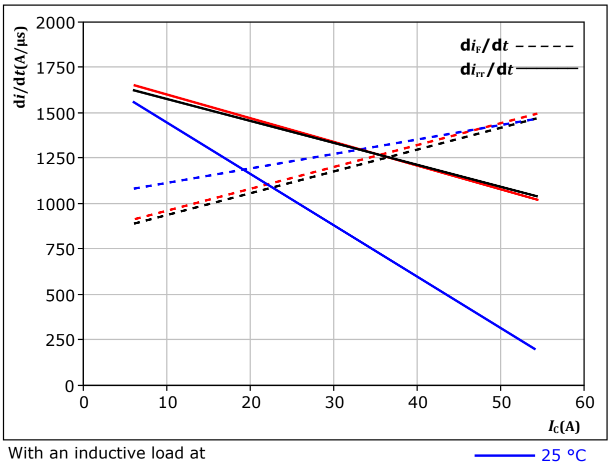
V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

Negative Neutral Point Switching Characteristics

figure 37. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



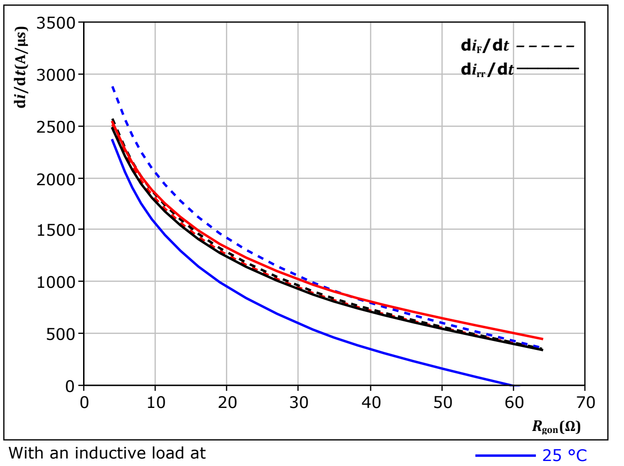
With an inductive load at

			T_j:	
V_{CE} =	400	V		25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 38. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



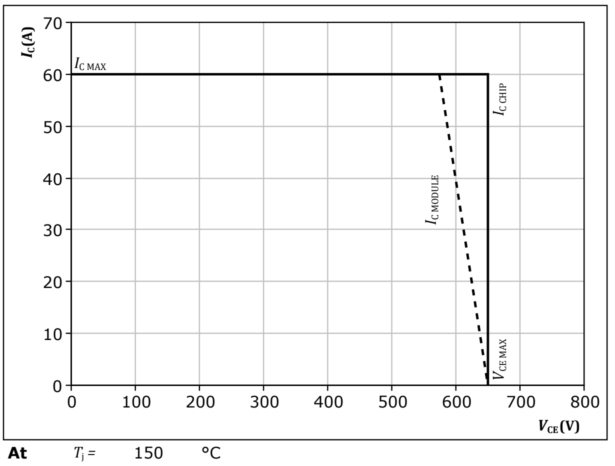
With an inductive load at

			T_j:	
V_{CE} =	400	V		25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

figure 39. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



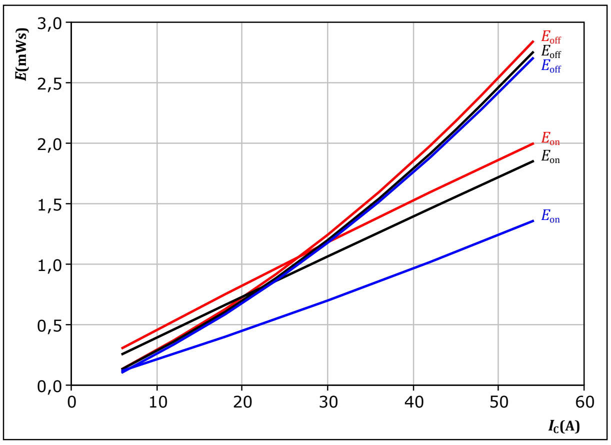
At			
	T_j =	150	°C
	R_{gon} =	16	Ω
	R_{goff} =	16	Ω

Positive Neutral Point Switching Characteristics

figure 40. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



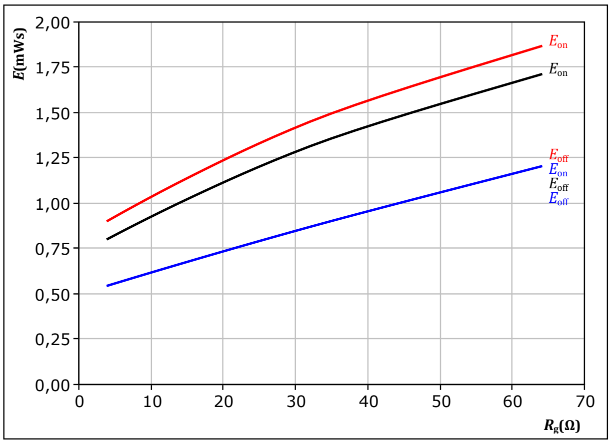
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C
R_{goff} =	64	Ω		

figure 41. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



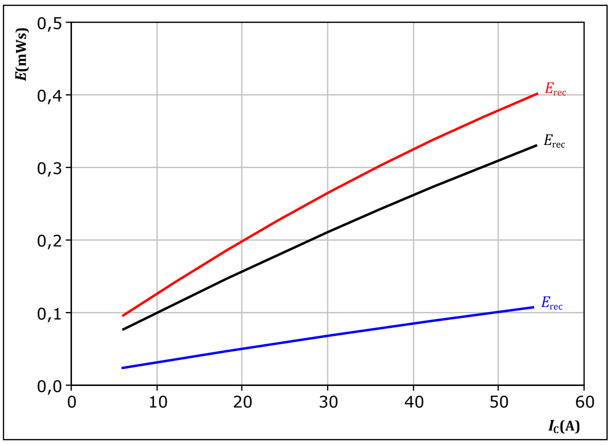
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

figure 42. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



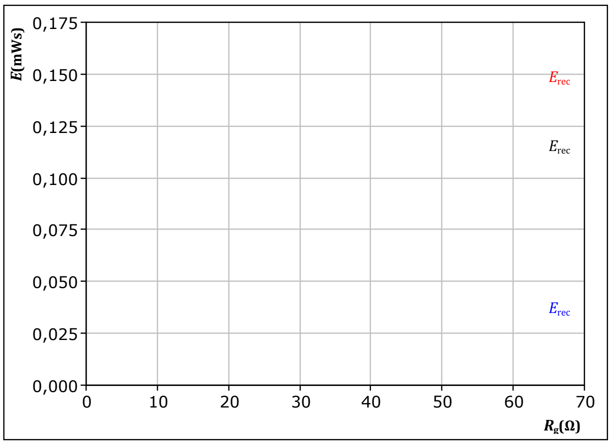
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 43. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

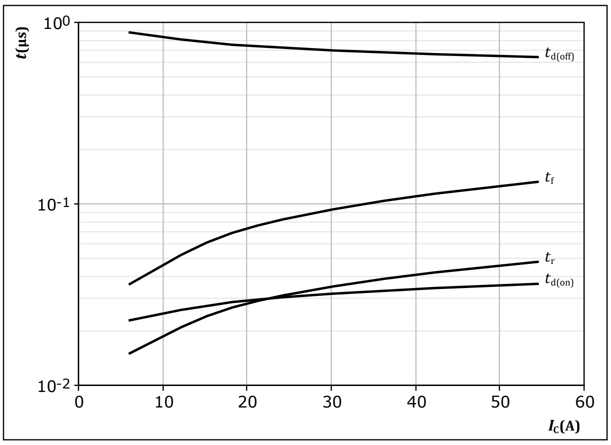
V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

Positive Neutral Point Switching Characteristics

figure 44. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



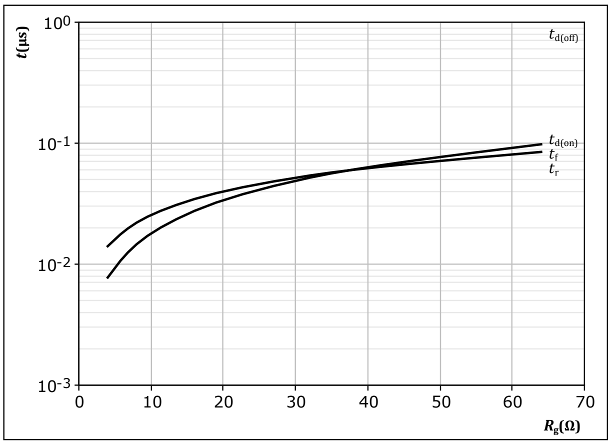
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	16	Ω
R_{goff} =	64	Ω

figure 45. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

$t = f(R_g)$



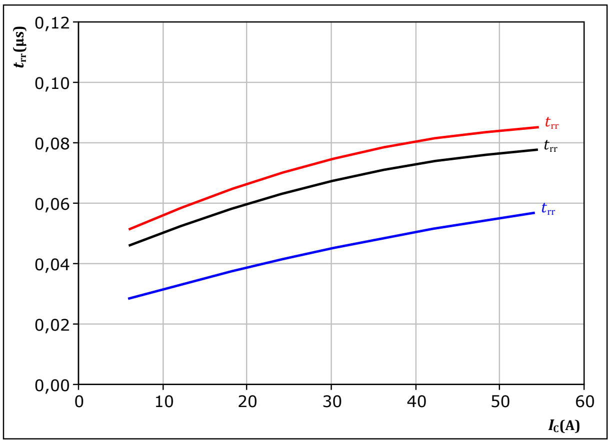
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	30	A

figure 46. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



With an inductive load at

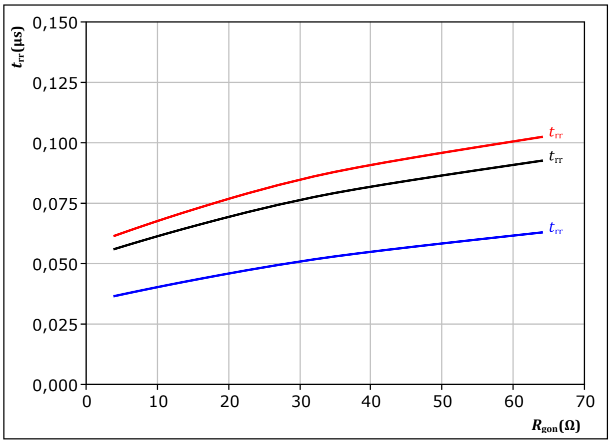
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	16	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 47. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



With an inductive load at

V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	30	A

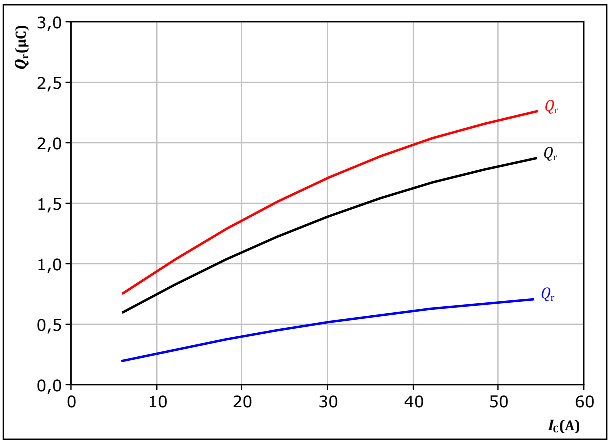
T_j: 25 °C, 125 °C, 150 °C

Positive Neutral Point Switching Characteristics

figure 48. **FWD**

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$



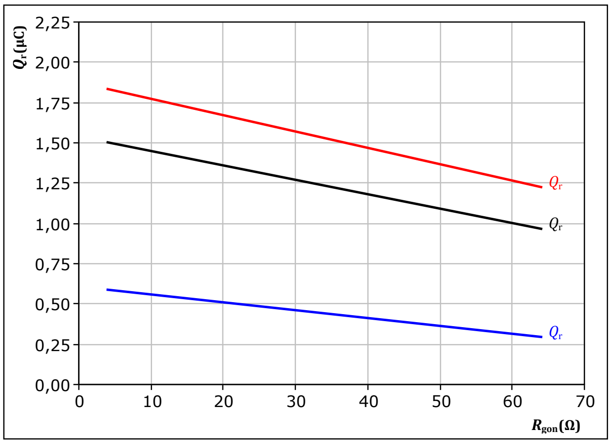
With an inductive load at

V_{CE} =	400	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	0/15	V	
R_{gon} =	16	Ω	

figure 49. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$



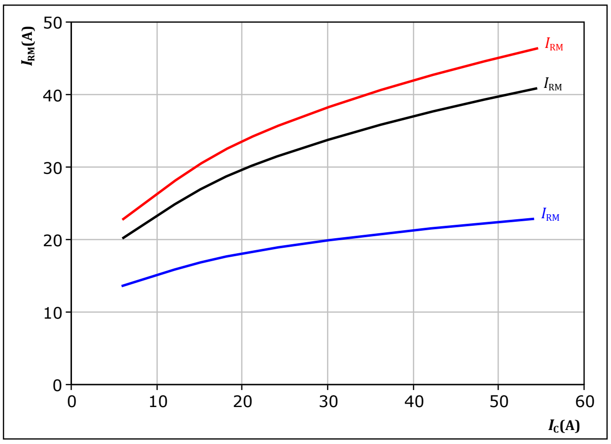
With an inductive load at

V_{CE} =	400	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	0/15	V	
I_C =	30	A	

figure 50. **FWD**

Typical peak reverse recovery current as a function of collector current

$I_{RM} = f(I_C)$



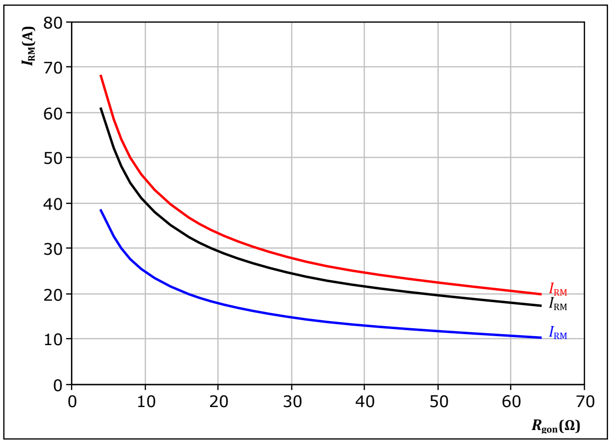
With an inductive load at

V_{CE} =	400	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	0/15	V	
R_{gon} =	16	Ω	

figure 51. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



With an inductive load at

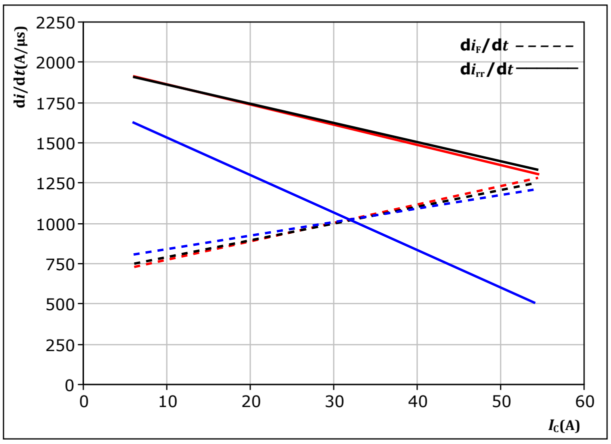
V_{CE} =	400	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	0/15	V	
I_C =	30	A	

Positive Neutral Point Switching Characteristics

figure 52. FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



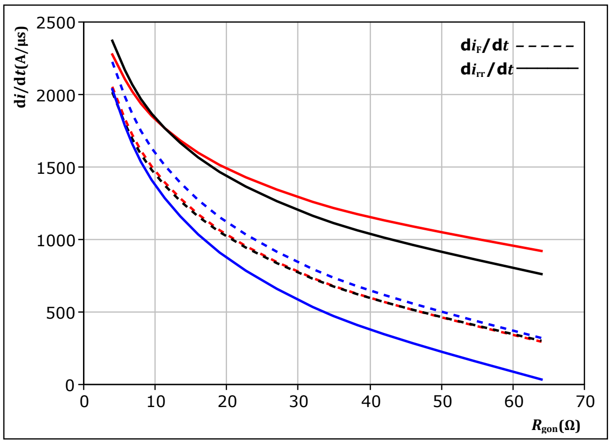
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 53. FWD

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



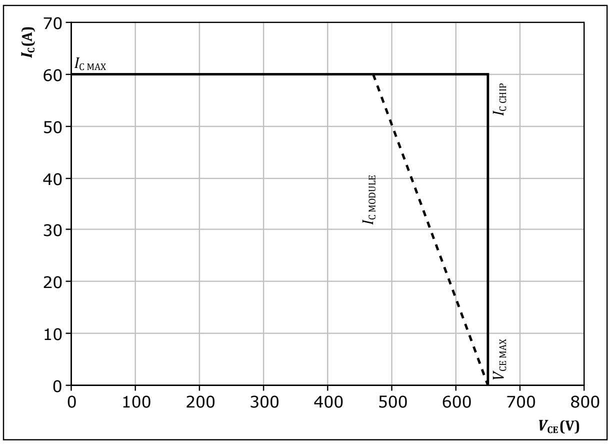
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	30	A		150 °C

figure 54. IGBT

Reverse bias safe operating area

I_C = f(V_{CE})



At			
	T_j =	150	°C
	R_{gon} =	16	Ω
	R_{goff} =	64	Ω

Switching Definitions

figure 55. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} = integrating time for E_{off})

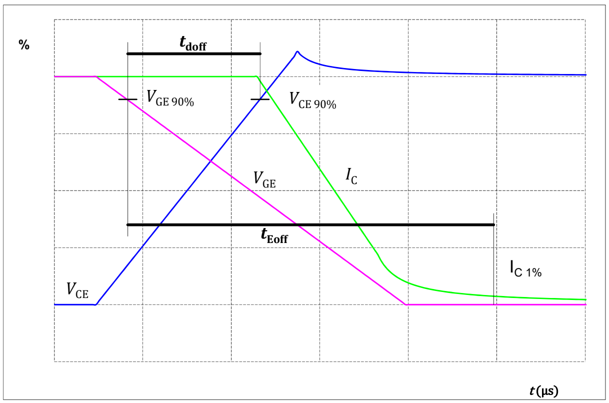


figure 56. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

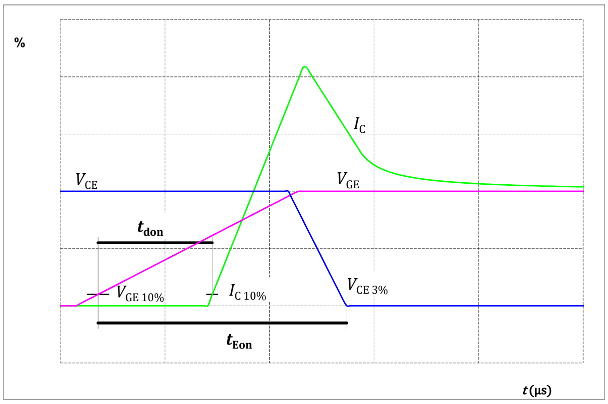


figure 57. **IGBT**

Turn-off Switching Waveforms & definition of t_f

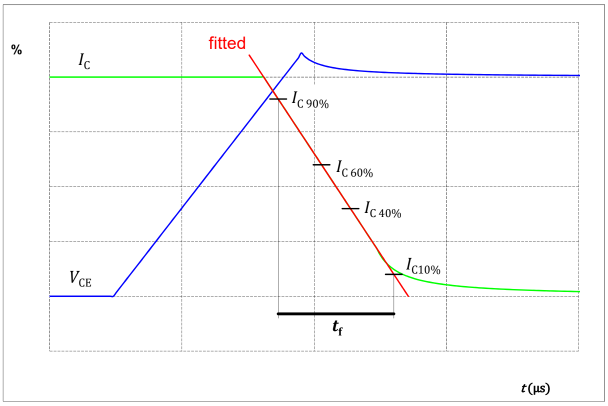
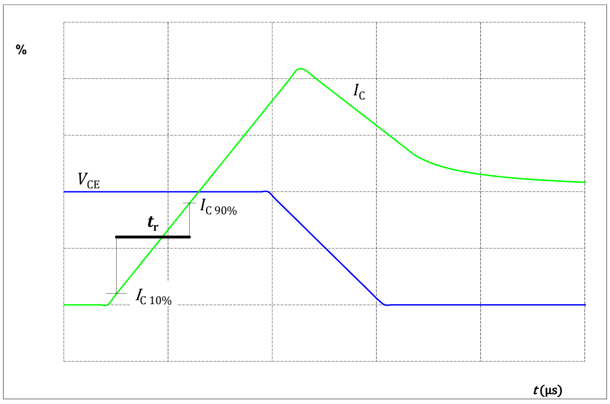


figure 58. **IGBT**

Turn-on Switching Waveforms & definition of t_r



Switching Definitions

figure 59. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

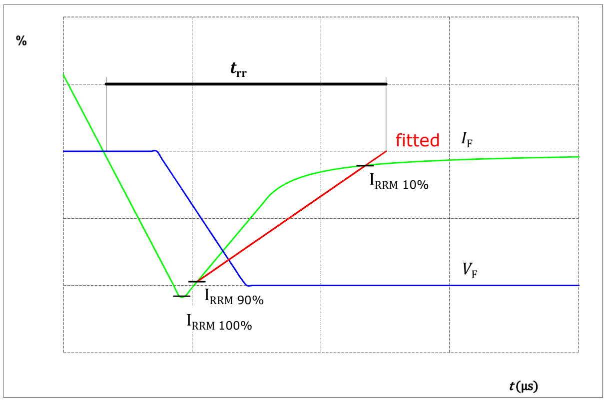
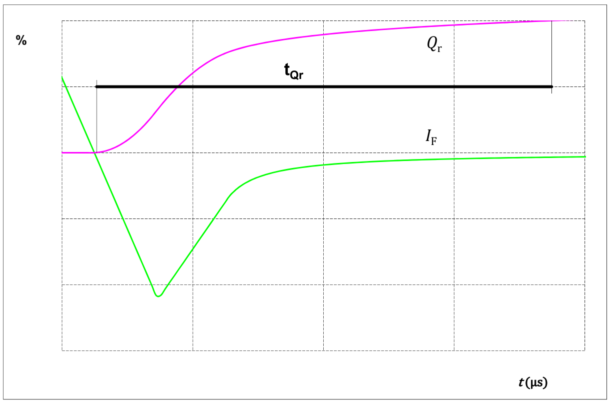


figure 60. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Ordering Code

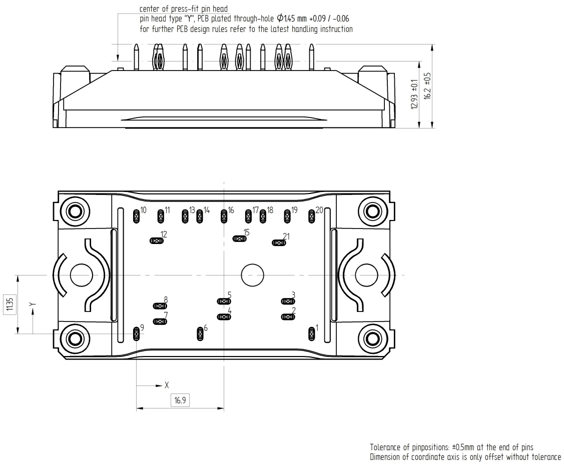
Version	Ordering Code
Without thermal paste	10-PC073AA030SM-PF04H06Y
With thermal paste (5,2 W/mK, PTM6000HV)	10-PC073AA030SM-PF04H06Y-/7/
With thermal paste (3,4 W/mK, PSX-P7)	10-PC073AA030SM-PF04H06Y-/3/

Marking

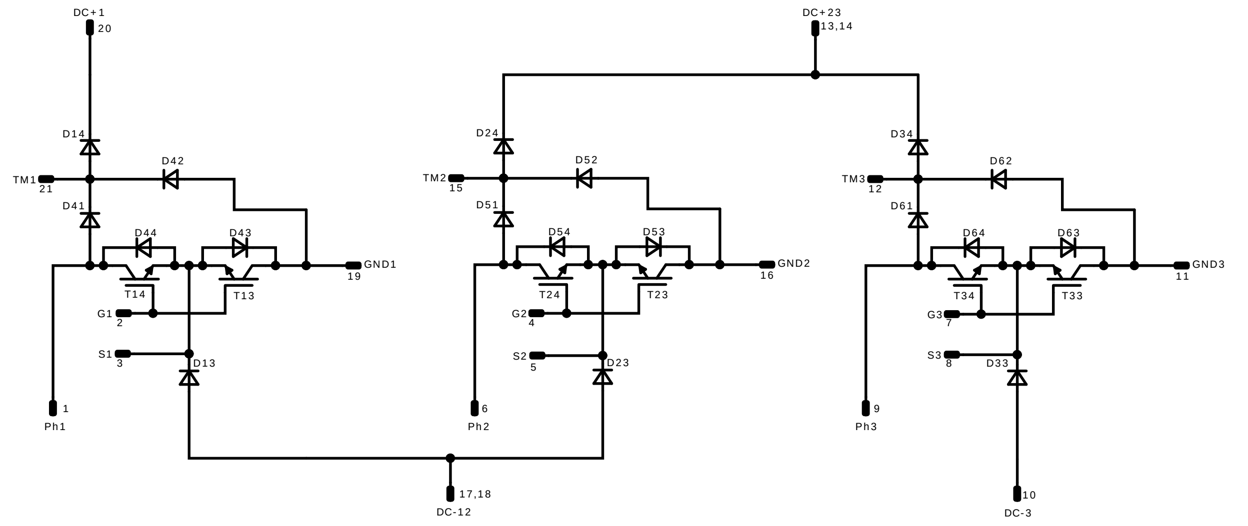
Text	**Name**		**Date code**	**UL & VIN**	**Lot**	**Serial**
	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

Pin table [mm]			
Pin	X	Y	Function
1	33,8	0	Ph1
2	29,25	3,3	G1
3	29,25	6,3	S1
4	16,9	3,3	G2
5	16,9	6,3	S2
6	12,3	0	Ph2
7	4,55	2,4	G3
8	4,55	5,4	S3
9	0	0	Ph3
10	0	22,7	DC-3
11	4,7	22,7	GND3
12	3,9	18	TM3
13	9,4	22,7	DC+23
14	12,2	22,7	DC+23
15	19,9	18,4	TM2
16	16,9	22,7	GND2
17	21,6	22,7	DC-12
18	24,4	22,7	DC-12
19	29,1	22,7	GND1
20	33,8	22,7	DC+1
21	27,5	17,6	TM1



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T13, T23, T33	IGBT	650 V	30 A	Negative Neutral Point Switch	
T14, T24, T34	IGBT	650 V	30 A	Positive Neutral Point Switch	
D13, D23, D33	FWD	600 V	30 A	Negative Boost Diode	
D14, D24, D34	FWD	600 V	30 A	Positive Boost Diode	
D43, D53, D63	Rectifier	1600 V	18 A	Negative Neutral Point Diode	
D44, D54, D64	Rectifier	1600 V	18 A	Positive Neutral Point Diode	
D42, D52, D62	FWD	650 V	10 A	Positive Boost Diode Protection Diode	
D41, D51, D61	Rectifier	1600 V	18 A	Positive Boost Blocking Diode	

Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 0 packages see vincotech.com website.

Package data
Package data for *flow* 0 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-PC073AA030SM-PF04H06Y-D1-14	11 Jul. 2022		